

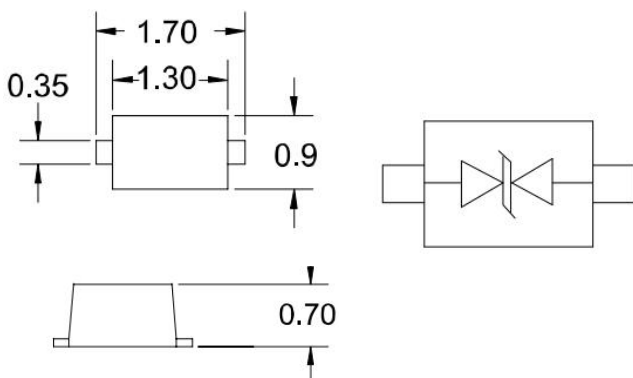
Description

The SEN1201D5 is a 12V bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The SEN1201D5 complies with the IEC 61000-4-2 (ESD) with ± 30 kV air and ± 30 kV contact discharge. It is assembled into an ultra-small lead-free SOD-523 package. The small size and high ESD surge protection make SEN1201D5 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- Protects one data line
- Ultra low leakage: nA level
- Low operating voltage: 5V
- Low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: ± 15 kV
 - Contact discharge: ± 8 kV
 - IEC61000-4-4 (EFT) 40A (5/50ns)
- RoHS Compliant

Dimensions & Symbol (Unit: mm Max)



Mechanical Characteristics

- Package: SOD-523
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- Peripherals
- Audio Players
- Keypads, Side Keys, LCD Displays

Marking Information



Details marking code reference specification of approval list

Ordering Information

Part Number	Packaging	Reel Size
SEN1201D5	3000/Tape & Reel	7 inch

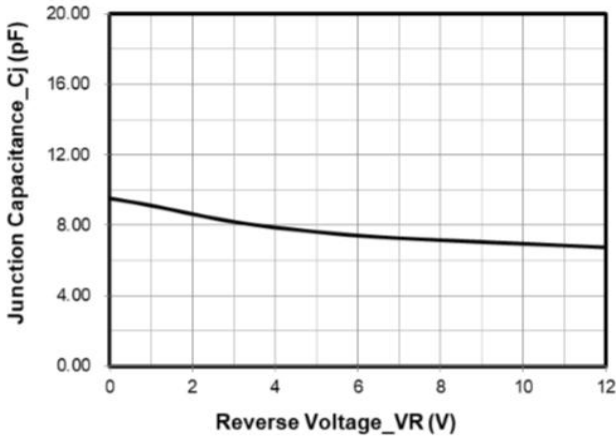
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$, RH=45%-75%, unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak Pulse Power (tp=8/20 μs waveform)	P_{ppp}	150	W
Peak Pulse Current (8/20 μs)	I_{pp}	8	A
ESD per IEC 61000-4-2 (Air)	V_{ESD}	± 30	kV
ESD per IEC 61000-4-2 (Contact)		± 30	
Operating Temperature Range	T_J	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^{\circ}\text{C}$

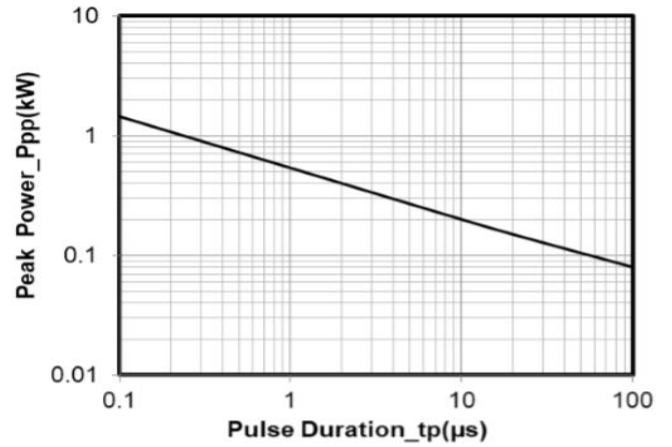
Electrical Characteristics ($T_A=25^{\circ}\text{C}$)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			12	V	
Breakdown Voltage	V_{BR}	13.3			V	$I_T = 1\text{mA}$
Reverse Leakage Current	I_R			0.2	μA	$V_{RWM} = 5\text{V}$
Clamping Voltage	V_C			15	V	$I_{PP} = 1\text{A}$ (8 x 20 μs pulse)
Clamping Voltage	V_C			19	V	$I_{PP} = 8\text{A}$ (8 x 20 μs pulse)
Junction Capacitance	C_J		9		pF	$V_R = 0\text{V}$, $f = 1\text{MHz}$

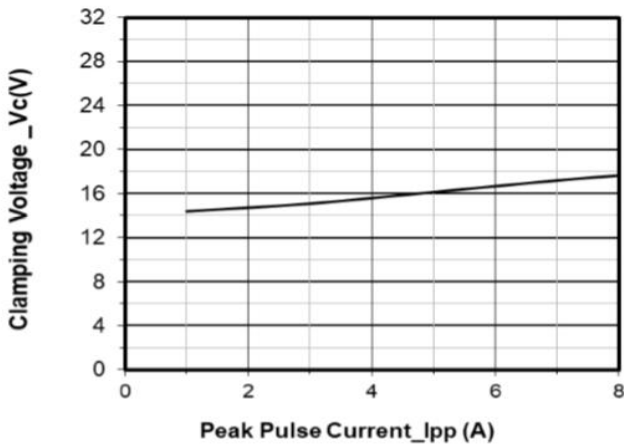
Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)



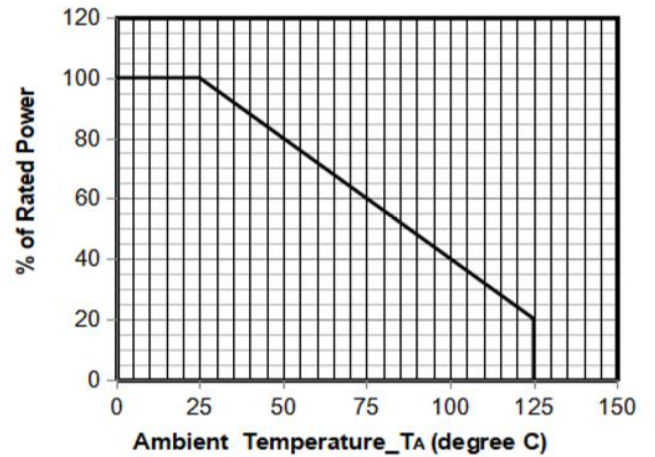
Junction Capacitance vs. Reverse Voltage



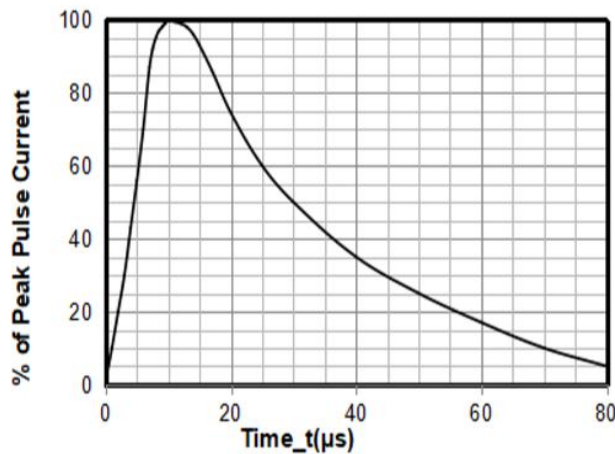
Peak Pulse Power vs. Pulse Time



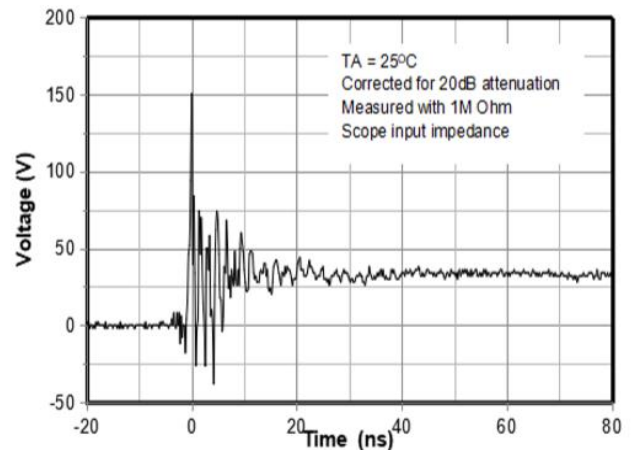
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



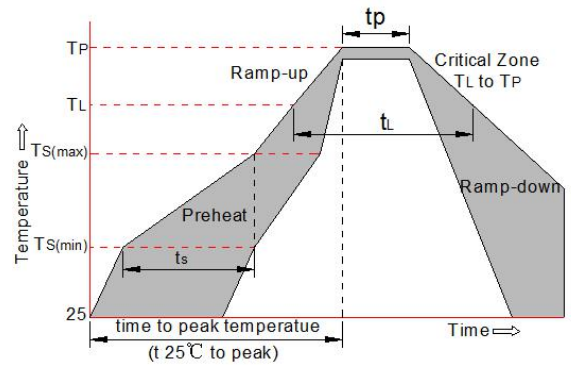
8 X 20 μs Pulse Waveform



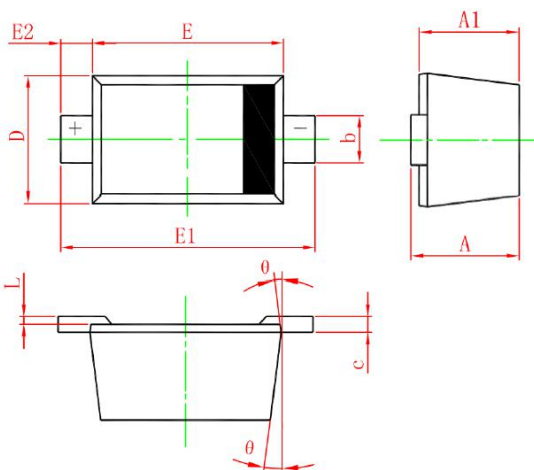
ESD Clamping Voltage
8 kV Contact per IEC61000-4-2

Soldering Parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L) (Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_p)		8 min. Max
Do not exceed		+260°C

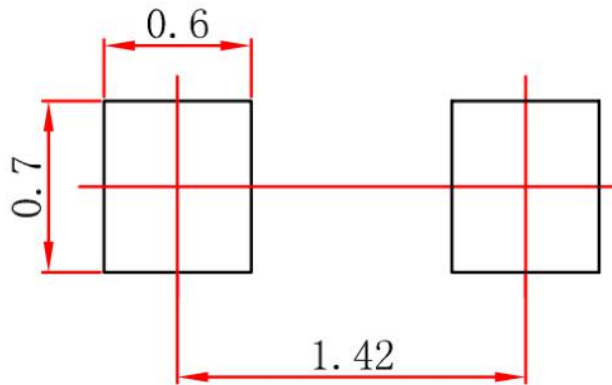


Package Mechanical Data



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.51	-	0.77	0.020	-	0.031
A1	0.50	-	0.70	0.020	-	0.028
b	0.25	-	0.35	0.010	-	0.014
c	0.08	-	0.15	0.003	-	0.006
D	0.75	-	0.85	0.030	-	0.033
E	1.10	-	1.30	0.043	-	0.051
E1	1.50	-	1.70	0.059	-	0.067
E2	0.20REF			0.008REF		
L	0.01	-	0.07	0.001	-	0.003
Φ	7° REF			7° REF		

Suggested Land Pattern



Contact Information

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